

# SANYO Semiconductors **DATA SHEET**

# LA75503V — For PAL TV/VCR Adjustment Free VIF/SIF Signal Processing IC

#### Overview

The LA75503V is an adjustment free VIF/SIF signal processing IC for PAL TV/VCR. It supports 38MHz, 38.9MHz, and 39.5MHz as the IF frequencies, as well as PAL sound multi-system (M/N, B/G, I, D/K), and contains an on-chip sound carrier trap and sound carrier BPF. To adjust the VCO circuit, AFT circuit, and sound filter, 4MHz external crystal or 4MHz external signal is needed.

#### **Features**

- Internal VCO adjustment free circuit eliminating need for VCO coil adjustments.
- Internal sound carrier BPF and sound carrier trap enable easy configuration of PAL sound multi-system at low cost.
- Considerably reduces the number of required peripheral parts.
- Use of digital AFT eliminates problem of AFT tolerance.
- Package: SSOP30 (275 mil)

#### **Functions**

- VIF amplifier
- VCO adjustment free PLL detection circuit
- Digital AFT circuit
- RF AGC
- Buzz canceller

- Equalizer amplifier
- Internal sound carrier BPF
- Internal sound carrier trap
- PLL-FM detector
- Reference oscillation circuit

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# **Specifications**

#### **Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V <sub>CC</sub> max		7	V
Circuit voltage	V16		V <sub>CC</sub>	V
	V18		Vcc	V
Circuit current	130		-1	mA
	l17		+0.5	mA
	16		-10	mA
	14		-3	mA
Allowable power dissipation	Pd max	Ta ≤ 75°C *	550	mW
Operating temperature	Topr		-20 to 70	°C
Storage temperature	Tstg		-55 to +150	°C

<sup>\*</sup> Mounted on a printed circuit board: 65mm  $\times$  72mm  $\times$  1.6mm, paper phenol.

#### Operating Conditions at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Recommended supply voltage	VCC		5	V
Operating voltage range	V <sub>CC</sub> op		4.5 to 5.5	V

### **Electrical Characteristics** at Ta = 25°C, $V_{CC} = 5.0V$ , fp = 38.9MHz

Parameter	Symbol	Conditions		Ratings		Unit
Falametei	Symbol	Conditions	min	typ	max	Offic
VIF Block						
Circuit current	l17			64.0	73.6	mA
Maximum RF AGC voltage	V14H	Collector load 30kΩ VC2 = 9 V	8.5	9		V
Minimum RF AGC voltage	V14L			0.3	0.7	V
Input sensitivity	Vi		33	39	45	dΒμV
AGC range	GR		58			dB
Maximum allowable input	Vi max		92	97		dΒμV
No-signal video output voltage	V4		3.3	3.6	3.9	V
Synchronizing signal tip voltage	V4tip		1.0	1.3	1.6	V
Video output level	Vo		1.7	2.0	2.3	Vp-p
Video signal-to-noise ratio	S/N	B/G	48	52		dB
C-S beating	IC-S	P/S = 10dB	26	32	38	dB
Differential gain	DG	Vin = 80dBμ		3	10	%
Differential phase	DP			2	10	deg
Black noise threshold voltage	V <sub>BTH</sub>			0.7		V
Black noise clamp voltage	V <sub>BCL</sub>			1.8		V
VIF input resistance	Ri			2.5	3.0	kΩ
VIF input capacitance	Ci			3	6	pF
Maximum AFT voltage	V13H		4.3	4.7	5.0	V
Maximum AFT voltage	V13L		0	0.2	0.7	V
AFT tolerance 1	dfa1	f = 38.9MHz		±35	±70	kHz
AFT tolerance 2	dfa2	f = 38.0MHz		±35	±70	kHz
AFT tolerance 3	dfa3	f = 39.5MHz		±35	±70	kHz
AFT detection sensitivity	Sf	R <sub>L</sub> = 100kΩ // 100kΩ	40	80	120	mV/kHz
AFT dead zone	fda			30	60	kHz
APC pull-in range (U)	fpu		1.5	2.0		MHz
APC pull-in range (L)	fpl		1.5	2.0		MHz
VCO maximum frequency range (U)	dfu		1.5	2.0		NHz
VCO maximum frequency range (L)	dfl		1.5	2.0		MHz
VCO control sensitivity	β		2.0	4.0	8.0	kHz/mV

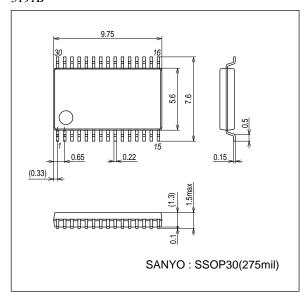
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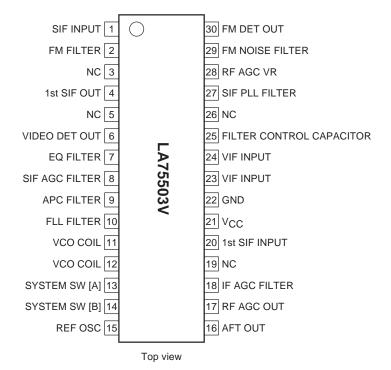
Parameter	Symbol	Conditions		Ratings		Unit
- diameter	5,551	00	min	typ	max	Jt
N trap1 (4.75MHz)	NT1	wrt 1MHz	-30	-35		dB
N trap2 (5.25MHz)	NT2	wrt 1MHz	-19	-24		dB
BG trap1 (5.75MHz)	BT1	wrt 1MHz	-27	-32		dB
BG trap2 (6.1MHz)	BT2	wrt 1MHz	-20	-25		dB
BG trap3 (5.85MHz)	BT3	wrt 1MHz	-27	-32		dB
l trap1 (6.25MHz)	IT1	wrt 1MHz	-25	-30		dB
l trap2 (6.8MHz)	IT2	wrt 1MHz	-15	-20		dB
DK trap1 (6.75MHz)	DT1	wrt 1MHz	-25	-30		dB
Group delay 1 NTSC (3.0MHz)	NGD1	wrt 1MHz	10	40	70	ns
Group delay 1-1 NTSC (3.5MHz)	NGD1-1	wrt 1MHz	70	120	170	ns
Group delay 2 BG (4MHz)	BGD2	wrt 1MHz	30	60	90	ns
Group delay 2-1 BG (4.4MHz)	BGD2-1	wrt 1MHz	100	150	200	ns
Group delay 3 I (4MHz)	IGD3	wrt 1MHz	0	30	60	ns
Group delay 3-1 I (4.4MHz)	IGD3-1	wrt 1MHz	30	60	90	ns
Group delay 4 DK (4MHz)	DGD4	wrt 1MHz	0	15	30	ns
Group delay 4-1 DK (4.4MHz)	DGD4-1	wrt 1MHz	0	30	60	ns
1st SIF Block	•					•
Conversion gain	Vg	fp = 5.5MHz, Vi = 500μV	26	32	38	dB
SIF carrier output level	So	Vi = 10mV		100		mVrms
First SIF maximum input	Si max	so ±2dB		106		dΒμV
First SIF input resistance	Ris			5.0	6.0	kΩ
First SIF input capacitance	Cis			3	6	pF
SIF Block	•					•
Limiting sensitivity	Vi(lim)	fp = 5.5MHz, $\Delta$ F = $\pm$ 30kHz at 400Hz	46	52	58	dΒμV
FM detector output voltage	V <sub>O</sub> (FM)		560	700	850	mVrms
AM rejection ratio	AMR	AM = 30% at 400Hz	50	60		dB
Total harmonic distortion	THD	fp = 5.5MHz, $\Delta F = \pm 30$ kHz		0.3	1.0	%
FM detector output S/N	S/N(FM)		55	60		dB
BPF 3dB bandwidth	BW			±100		kHz
PAL de-emphasis	Pdeem	fm = 3kHz		-3		dB
NTSC de-emphasis	Ndeem	fm = 2kHz		-3		dB
PAL/NT audio voltage gain difference	GD			6		dB
Others						•
4MHz level (during external input)	X4MIN	Terminated	86			dΒμ
SIF system SW threshold voltage	V10, V11			1.4		V
IF system SW threshold resistance	V12				270	kΩ

# **Package Dimensions**

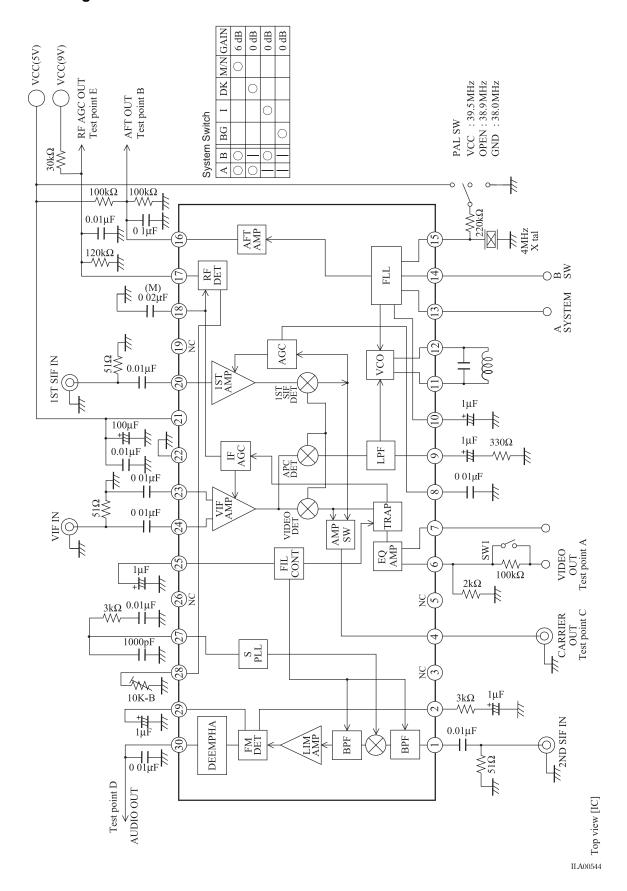
unit : mm (typ) 3191B



# **Pin Assignment**

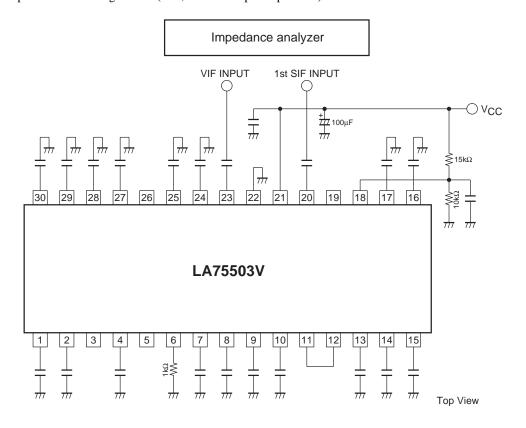


# **Block Diagram and Test Circuit 1**



#### **Test circuit 2**

Input Impedance Measuring Circuit (VIF, First SIF input impedance)



#### **System Switching**

• SIF system switch

The SIF system is switched by setting pins A (pin 13) and B (pin 14) to GND or OPEN.

А	В	B/G	I	D/K	M/N	FM DET LEVEL	De-emphasis
GND	GND				0	6dB	75μs
GND	OPEN			0		0dB	50μs
OPEN	GND		0			0dB	50μs
OPEN	OPEN	0				0dB	50μs

Note: "O" indicates that the system is selected.

#### • IF system switch

38.9MHz is selected as the IF frequency by leaving pin 15 (crystal oscillation) open. 38MHz is selected by adding  $220k\Omega$  between pin 15 and GND. This device can also select 39.5MHz operation by adding a  $220k\Omega$  resistor between pin 15 and  $V_{CC}$ .

#### • Split/inter carrier switch

Inter carrier is selected by setting the first SIF input (pin 20) to GND.

#### **Sound Trap**

The trapping point of the sound trap is set approximately 250kHz above the SIF center frequency of each mode to improve the video S/N. Therefore, design using split specifications is preferable.

# LA75503V

# **Pin Function**

Pin No.	Pin name	Pin function	Equivalent circuit
1	SIF INPUT	Inputs the SIF signal from the first SIF output. Set the input level to $90\text{dB}_\mu\text{V}$ or lower because of the dynamic range of the internal filter.	BPF SIF INPUT
2	FM FILTER	This is the FM feedback filter pin. It is composed of a C and R filters. $1\mu F$ is normally used as the capacitance. If the capacitance is a low value, the audio output level is small at low frequencies. Moreover, the audio output level can be made smaller by increasing the resistance connected in series. Use a resistance of $3k\Omega$ or higher.	1kΩ 1kΩ 2 FM FILTER ± 1/2/2 C W R
3	NC	Not connected.	
4	1st SIF OUT	This is the first SIF output. In case of inter carrier, the chroma carrier is bigger than split carrier applications, so that it is recommended to connect a filter externally. Filter example $\begin{array}{c c} 330\Omega & 39pF & 39pF \\\hline 4 & W & 1 \end{array}$	200Ω WW-4 1st SIF OUT
5	NC	Not connected.	

	from preceding page.		
Pin No.	Pin name	Pin function	Equivalent circuit
6	VIDEO-OUT	Pin 6 is the video output pin.	
7	EQ-OUT	The EQ amplifier can be thought of as shown below.  R W Therefore, the peak gain of the EQ amplifier is determined by Av = 1 + R/Z. However, note that the LA75503V being an IC with V <sub>CC</sub> = 5V, setting too large an amplitude	2kΩ VIDEO OUT  1kΩ VIDEO OUT  6  7  EQ OUT  400μA
		causes distortion in the Vcc side. Use so that the white level is 4V or less.	
8	SIF AGC FILTER	Pin 8 is the SIF AGC filter pin. Use this pin with a capacitance between $0.01 \mu F$ and $0.1 \mu F$ .	AGC DET 78kΩ 7777 AGC
9 10	APC FILTER FLL FILTER	Pin 9 is the PLL detector APC filter pin. Normally the following are used: $R = 330\Omega$ $C1 = 0.47\mu F \text{ to } 1\mu F$ $C2 = 100 pF$ $C1 = 1\mu F \text{ is effective for the over-modulation characteristics.}$ When the PLL is locked, the signal passes via the path marked A in the figure, and when PLL is unlocked and in weak signal, the signal passes via the path marked B in the figure. The PLL loop gain can thus be switched in this manner. Pin 10 is a VCO automatic control FLL filter pin. Since it operates always on a small current, using a larger capacitance results in a slower response. Normally, a capacitance between 0.47 $\mu$ F and 1 $\mu$ F is used. Moreover, the control range for this pin is between about 3V to 4.7V. Since this range is determined when adjusting the VCO tank circuit, set the design center of L and C of VCO so that the voltage of pin 10 is 3.6 V.	A 1kΩ 1kΩ 1kΩ VCO  APC DET Output  R C1  Time constant switch  APC DET NT  Time constant switch  Time const

Continued	I from preceding page.		
Pin No.	Pin name	Pin function	Equivalent circuit
11 12	VCO COIL	This is the VCO tank circuit for the PLL detector. Use a tuning capacitance of 24pF. Use L and C specifications that are accurate to ±2%. Also, design the L and C values so that the voltage of pin 10 is 3.6V when PLL is locked while using the IF center frequency.	
13 14	SYSTEM SW [A] SYSTEM SW [B]	This is the system switch pin. The transistor turns ON when the pin voltage from the circuit becomes approx. 1.4V.	40kΩ $30$ kΩ $30$ kΩ $30$ kΩ $30$ kΩ $30$ kΩ
15	REF OSC	This pin can be used both as the crystal resonator pin and IF switch. The 38MHz mode is selected by inserting $220k\Omega$ between pin 15 and GND, the 38.9MHz mode by leaving the pin open, and the 39.5MHz mode by inserting $220k\Omega$ between pin 15 and $V_{CC}$ . 4MHz input is possible from this pin. In the case of 4MHz external input, input $86dB_{\mu}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

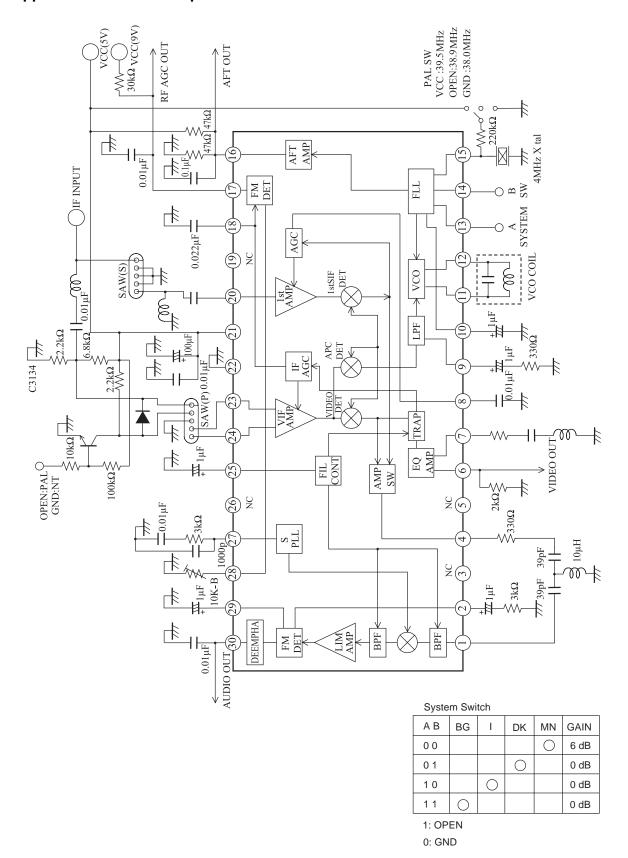
AFT waveform  AFT waveform  The proof of the	2 0.1μF
RF AGC max is determined by R1 and R2. RF AGC min is determined by R3 and R4. Capacitor C1 prevents oscillation and capacitor C2 is the RF AGC filter.	
Normally 30k $\Omega$ is used for R1, but if the tuner's F/E transistor is GaAS, the gate's impedance is lower, so use approx. $10k\Omega$ .	VCC R1 to TUNER R2 7777
18 IF AGC FILTER Pin 18 is the IF AGC filter pin. Normally, 0.01μF to 0.02 μF polyester film capacitor is used. Determine the impedance based on H-SAG and AGC speed.	2nd AGC FILTER
- 0.015μF	

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Pin No.	Pin name	Pin function	Equivalent circuit
20	1st SIF INPUT	Pin 20 can be used both as the First SIF IN and inter/split switch pins. In the case of inter carrier, connect pin 20 to GND. When a sound saw filter is added, the matching loss can be decreased by inserting L to neutralize the IC input capacitance and saw filter output capacitance.	5kΩ W
		SAW Saw Ci	5kΩ  W  777  777  777  50kΩ  20kΩ  W  W  >>
21	Vcc	Connect the decoupling capacitor as close as	20 Lto INT / SPLIT SW
	OND	possible.	
22 23 24	GND VIF INPUT	Pins 23 and 24 are VIF input pins. To reduce the loss of signal through a saw filter, input resistors are set to $2k\Omega$ . VIF amplifier has three capacitive coupling amplifiers, direct connection from a saw filter is available.	to 2nd AMP

Continue	d from preceding page.		
Pin No.	Pin name	Pin function	Equivalent circuit
25	FILTER CONTROL CAPACITOR	Internal filters (i.e. sound carrier BPF and sound carrier trap) are tuned using the capacitor connected to pin 25.  A value between 0.47µF and 1µF is considered desirable taking video S/N, and AM and PM noise into consideration.	to FILTER CONTROL  Vref  Vref  FIL CONT  7///
26	NC	Not connected.	
27	SIF PLL FILTER	Pin 27 is the SIF PLL filter pin. Normally use the following values. R: $3k\Omega$ C1: $0.01\mu F$ C2: $1000pF$ level Small R value Small R value A large R value ( $6k\Omega$ or lower) results in high-pass FM detection output noise. A smaller R value results in low-pass noise.	SIF VCO

Pin No.	I from preceding page. Pin name	Pin function	Equivalent circuit
28	RF AGC VR	Pin 28 is the RF AGC VR pin. When this pin is connected to GND, no signal is appeared on pin 6 and pin 30.	The state of the
29	FM FILTER	Pin 29 is the FM filter pin. Use a capacitance between 0.01μF and 1μF.	FM FILTER 3.6V 35kΩ FM DET  1μF SW
30	FM DET OUT	Pin 30 is the FM output pin.   The built-in differential amplifier determines and switches the de-emphasis resistance value.   PAL: $5k\Omega \times 0.01\mu F$ NT: $7.5k\Omega \times 0.01\mu F$	$2.0 \mathrm{k}\Omega$ $30$ $11.4 \mathrm{k}\Omega$ $1.4 \mathrm{k}\Omega$

# **Application Circuit Example**



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